TOSHIBA Transistor Silicon NPN Triple Diffused Type

2SC5242

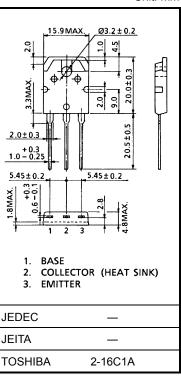
Power Amplifier Applications

• High Collector breakdown voltage: VCEO = 230 V (min)

- Complementary to 2SA1962
- Suitable fro use in 80-W high fidelity audio amplifier's output stage

Maximum Ratings (Tc = 25°C)

Characteristics	Symbol	Rating	Unit	
Collector-base voltage	V _{CBO}	230	V	
Collector-emitter voltage	V _{CEO}	230	V	
Emitter-base voltage	V _{EBO}	5	V	
Collector current	Ι _C	15	А	
Base current	Ι _Β	1.5	А	
Collector power dissipation (Tc = 25°C)	Pc	130	W	
Junction temperature	Тј	150	°C	
Storage temperature range	T _{stg}	-55 to 150	°C	



Electrical Characteristics (Tc = 25°C)

Weight: 4.7 g (typ.)

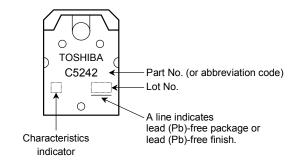
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = 230 V, I _E = 0	_	_	5.0	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 5 V, I _C = 0	_	_	5.0	μA
Collector-emitter breakdown voltage	V (BR) CEO	I _C = 50 mA, I _B = 0	230	—	—	V
DC current gain	h _{FE (1)} (Note)	V _{CE} = 5 V, I _C = 1 A	55	_	160	
	h _{FE (2)}	V _{CE} = 5 V, I _C = 7 A	35	60	—	
Collector-emitter saturation voltage	V _{CE (sat)}	I _C = 8 A, I _B = 0.8 A	—	0.4	3.0	V
Base-emitter voltage	V_{BE}	V _{CE} = 5 V, I _C = 7 A	_	1.0	1.5	V
Transition frequency	f _T	V _{CE} = 5 V, I _C = 1 A	_	30	—	MHz
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz	_	200	—	pF

Note: hFE (1) classification R: 55 to 110, O: 80 to 160

Unit: mm

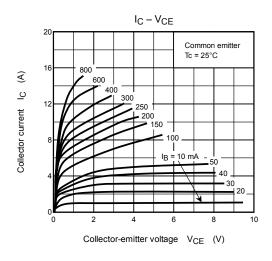
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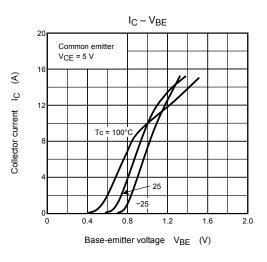
Marking

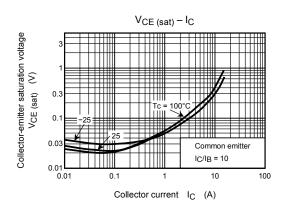


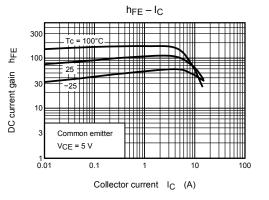
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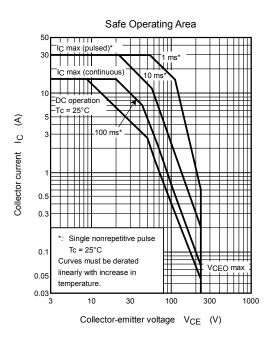
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